

4M High-speed SRAM (256-kword × 16-bit)

Manufacturers

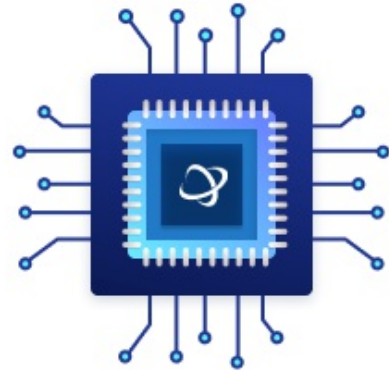
[Renesas Technology Corp](#)

Package/Case

Product Type

RoHS

Lifecycle



Images are for reference only

Please submit RFQ for R1RW0416DSB-2PR#D1 or [Email to us: sales@ovaga.com](mailto:sales@ovaga.com) We will contact you in 12 hours.

[RFQ](#)

## General Description

### Features

Single 3.3 V supply: 3.3 V ± 0.3 V

Access time: 10 ns / 12 ns (max)

Completely static memory No clock or timing strobe required

Equal access and cycle times

Directly TTL compatible All inputs and outputs

Operating current: 145 / 130mA (max)

TTL standby current: 40 mA (max)

CMOS standby current : 5 mA (max) : 0.8 mA (max) (L-version) : 0.5 mA (max) (S-version)

Data retention current : 0.4 mA (max) (L-version) : 0.2 mA (max) (S-version)

Data retention voltage: 2.0 V (min) (L-version , S-version)

Center V<sub>CC</sub> and V<sub>SS</sub> type pin out

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